

MSS40 / 50 Series

BACK TO BACK SCR MODULE

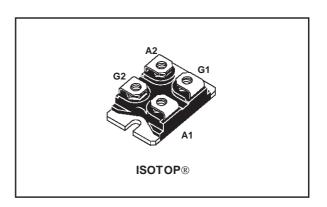
MAIN FEATURES:

| Symbol | Value | Unit |
|------------------------------------|--------------|------|
| I _{T(RMS)} | 55 and 70 | А |
| V _{DRM} /V _{RRM} | 800 and 1200 | V |
| I _{GT} | 50 | mA |

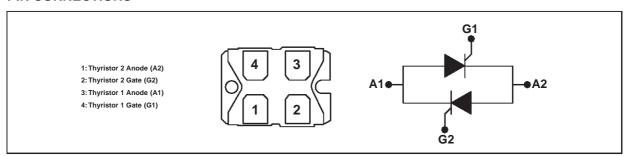
DESCRIPTION

Packaged in ISOTOP modules, the MSS40 / MSS50 Series is based on two back-to-back SCR configurations, providing high noise immunity. They are suitable for high power applications such as solid state relays, heating control systems, welding equipment, motor control circuits...

The compactness of the ISOTOP package allows high power density and optimized power bus connections. Thanks to their internal ceramic pad, they provide high voltage insulation (2500V RMS), complying with UL standards (File ref: E81734).



PIN CONNECTIONS



ABSOLUTE RATINGS (limiting values)

| Symbol | Parameter | | | Value | | Unit |
|------------------------------------|---|---|-------------|--------------------------------|------|------------------|
| | | | MSS40 | MSS50 | | |
| I _{T(RMS)} | RMS on-state current | Tc = 8 | 0 °C | 55 | | Α |
| , , | | Tc = 8 | 5 °C | | 70 | |
| I _{TSM} | Non repetitive surge peak on-state | tp = 16.7 ms | Tj = 25°C | 420 | 630 | А |
| | current | tp = 20 ms | 1 1 2 2 3 0 | 400 | 600 | 1 |
| l t | I t Value for fusing | tp = 10 ms | Tj = 25°C | 800 | 1800 | A ² s |
| dl/dt | Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, tr ≤ 100 ns $F = 120$ Hz $T_j = 125^{\circ}$ C | | 50 | | A/μs | |
| I _{GM} | Peak gate current | Peak gate current $tp = 20 \mu s$ $Tj = 125$ °C | | 4 | | А |
| P _{G(AV)} | Average gate power dissipation Tj = 125°C | | 1 | | W | |
| T _{stg} T _j | Storage junction temperature range Operating junction temperature range | | | - 40 to + 150 - 40 to + 125 | | °C |
| V _{RGM} | Maximum peak reverse gate voltage | | 5 | | V | |

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ELECTRICAL CHARACTERISTICS (Tj = 25°C, unless otherwise specified)

| Symbol | Test Conditions | | | Value | | Unit | |
|------------------|---|--------------------------------|------|-------|-------|------|--|
| | | | | MSS40 | MSS50 | | |
| I _{GT} | MIN. | | MIN. | | 5 | mA | |
| | $V_D = 12 \text{ V}$ $R_L = 33 \Omega$ | | MAX. | 5 | 0 | | |
| V _{GT} | | | MAX. | 1 | .3 | V | |
| V _{GD} | $V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $Tj = 125^{\circ}\text{C}$ MIN. | | MIN. | 0.2 | | V | |
| IH | I _T = 500 mA Gate open MAX. | | MAX. | 80 | | mA | |
| IL | I _G = 1.2 I _{GT} | | MAX. | 120 | | mA | |
| dV/dt | $V_D = 67 \% V_{DRM}$ Gate open $Tj = 125$ °C | | MIN. | 10 | 00 | V/µs | |
| V _{TM} | I _{TM} = 80 A tp = 380 μs | | MAY | 1.7 | - | V | |
| V IM | I _{TM} = 100 A tp = 380 μs | $Tj = 25^{\circ}C \qquad MAX.$ | | - | 1.7 | 1 ' | |
| V _{t0} | Threshold voltage Tj = 125°C M | | MAX. | 0. | 85 | V | |
| R _d | Dynamic resistance Tj = 125°C MA | | MAX. | 11 | 7 | mΩ | |
| I _{DRM} | | | MAX. | 2 | 0 | μА | |
| I _{RRM} | | | 1 | 1 | 0 | mA | |

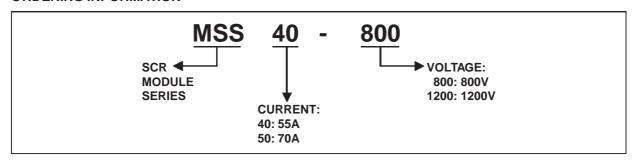
THERMAL RESISTANCES

| Symbol | Parameter | | | Unit |
|----------------------|-----------------------|-------|------|------|
| R _{th(j-c)} | Junction to case (AC) | MSS40 | 0.6 | °C/W |
| | | MSS50 | 0.45 | |

PRODUCT SELECTOR

| Part Number | Voltage (xxx) | | Sensitivity | Package |
|-------------|---------------|--------|-------------|----------|
| | 800 V | 1200 V | , | . uonugo |
| MSS40-xxx | Х | Х | 50 mA | ISOTOP™ |
| MSS50-xxx | X | X | 50 mA | ISOTOP™ |

ORDERING INFORMATION



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OTHER INFORMATION

| Part Number | Marking | Weight | Base Quantity | Packing mode |
|-------------|-----------|--------|---------------|--------------|
| MSS40-xxx | MSS40-xxx | 27.0 g | 10 | Tube |
| MSS50-xxx | MSS50-xxx | 27.0 g | 10 | Tube |

Note: xxx = voltage

Fig. 1: Maximum power dissipation versus RMS on-state current.

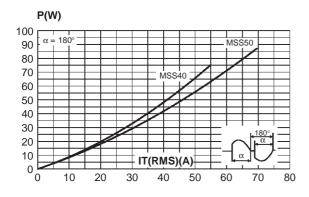


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration.

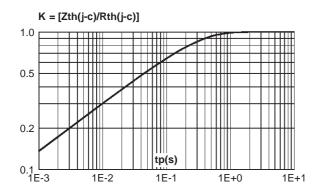


Fig. 2: RMS on-state current versus case temperature.

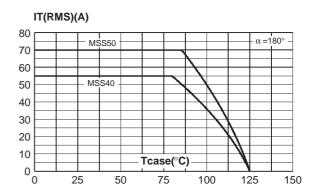
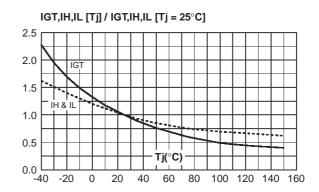


Fig. 4: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).



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Fig. 5: Surge peak on-state current versus number of cycles.

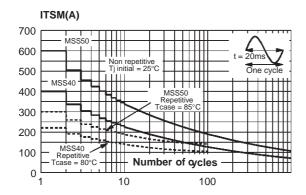


Fig. 7-1: On-state characteristics (maximum values) (MSS40).

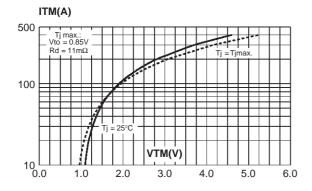


Fig. 6:Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10 ms, and corresponding value of I t.

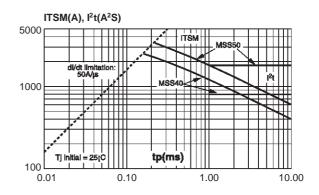
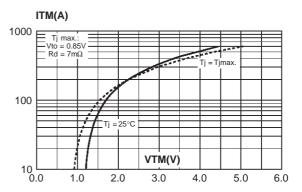


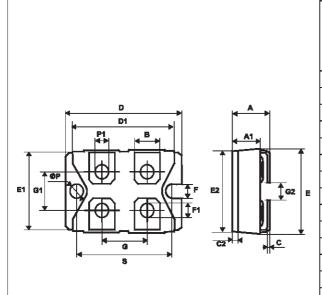
Fig. 7-2: On state characteristics (maximum values) (MSS50).



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PACKAGE MECHANICAL DATA

ISOTOPTM



| | DIMENSIONS | | | |
|------|-------------|-------|--------|--------|
| REF. | Millimeters | | Inches | |
| | Min. | Max. | Min. | Max. |
| А | 11.80 | 12.20 | 0.465 | 0.480 |
| A1 | 8.90 | 9.10 | 0.350 | 0.358 |
| В | 7.8 | 8.20 | 0.307 | 0.323 |
| С | 0.75 | 0.85 | 0.030 | 0.033 |
| C2 | 1.95 | 2.05 | 0.077 | 0.081 |
| D | 37.80 | 38.20 | 1.488 | 1.504 |
| D1 | 31.50 | 31.70 | 1.240 | 1.248 |
| Е | 25.15 | 25.50 | 0.990 | 1.004 |
| E1 | 23.85 | 24.15 | 0.939 | 0.951 |
| E2 | 24.80 typ. | | 0.97 | 6 typ. |
| G | 14.90 | 15.10 | 0.587 | 0.594 |
| G1 | 12.60 | 12.80 | 0.496 | 0.504 |
| G2 | 3.50 | 4.30 | 0.138 | 0.169 |
| F | 4.10 | 4.30 | 0.161 | 0.169 |
| F1 | 4.60 | 5.00 | 0.181 | 0.197 |
| Р | 4.00 | 4.30 | 0.157 | 0.69 |
| P1 | 4.00 | 4.40 | 0.157 | 0.173 |
| S | 30.10 | 30.30 | 1.185 | 1.193 |

- Recommended torque value: 1.3 Nm (max. 1.5 Nm) for the 6 x M4 screws (2 x M4 screws recommended for mounting the package on the heatsink and the 4 provided screws.
 The screws supplied with the package are adapted for mounting on a board (or other types of termi-
- nals) with a thickness of 0.6 mm min. and 2.2 mm max.

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